

ABSTRACT

THYRISTOR-BASED SRAM

An integrated circuit structure includes a semiconductor substrate and a horizontal semiconductor fin on top of the semiconductor substrate. An access transistor gate and a thyristor gate are on top of the semiconductor substrate and in contact with the horizontal semiconductor fin. An access transistor is at least a portion of the horizontal semiconductor fin and the access transistor gate. A thyristor is at least a portion of the horizontal semiconductor fin and the thyristor gate, the access transistor is in contact with the thyristor.

FIG. 7